



General Description

AFC7540, N & P Pair enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge. These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

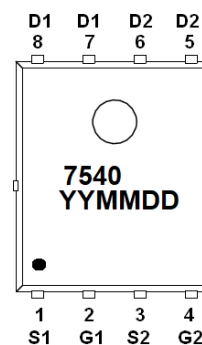
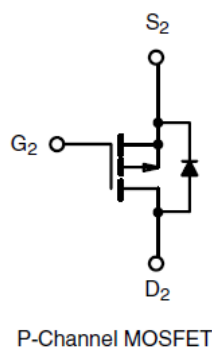
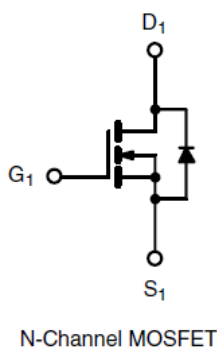
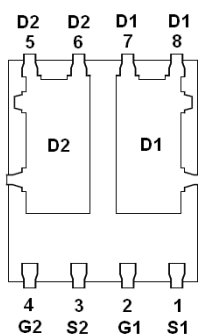
N-Channel

- $I_D=12A, R_{DS(ON)}=14m\Omega@V_{GS}=4.5V$
- $I_D=10A, R_{DS(ON)}=16m\Omega@V_{GS}=2.5V$
- $I_D=8A, R_{DS(ON)}=20m\Omega@V_{GS}=1.8V$

P-Channel

- $I_D=-9A, R_{DS(ON)}=33m\Omega@V_{GS}=-4.5V$
- $I_D=-8A, R_{DS(ON)}=42m\Omega@V_{GS}=-2.5V$
- $I_D=-6A, R_{DS(ON)}=68m\Omega@V_{GS}=-1.8V$

Pin Description (DFN5X6-8L)



Application

- Point-of-Load Synchronous Rectifier
 - 5 V or 3.3 V BUS Step Down
- Synchronous Buck, Shoot-Thru Resistant

Pin Define

Pin	Symbol	Description
1	S1	Source 1
2	G1	Gate 1
3	S2	Source 2
4	G2	Gate 2
5	D2	Drain 2
6	D2	Drain 2
7	D1	Drain 1
8	D1	Drain 1

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFC7540FN568RG	7540	DFN 5X6-8L	Tape & Reel	2500 EA

※ 7540 : Parts Code

※ YYMMDD : Date Code

※ AFC7540FN568RG : 13" Tape & Reel ; Pb- Free ; Halogen -Free



Absolute Maximum Ratings (N-Channel)

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	20	V
Gate –Source Voltage	V _{GSS}	±12	V
Continuous Drain Current(T _J =150°C)	I _D	T _A =25°C	12
		T _A =70°C	10
Pulsed Drain Current	I _{DM}	20	A
Continuous Source Current(Diode Conduction)	I _S	1.5	A
Power Dissipation	P _D	T _A =25°C	3.5
		T _A =70°C	2.2
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	62.5	°C/W

Electrical Characteristics (N-Channel)

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250uA	20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	0.35		1.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	uA
		V _{DS} =20V, V _{GS} =0V T _J =85°C			10	
On-State Drain Current	I _{D(on)}	V _{DS} ≥ 5V, V _{GS} =4.5V	30			A
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =12A		8.4	14	mΩ
		V _{GS} =2.5V, I _D =10A		9.6	16	
		V _{GS} =1.8V, I _D = 8A		12	20	
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =7.0A		40		S
Diode Forward Voltage	V _{SD}	I _S =9.0A, V _{GS} =0V		0.8	1.3	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =10V, V _{GS} =4.5V I _D ≧9.0A		13	19	nC
Gate-Source Charge	Q _{gs}			2.8		
Gate-Drain Charge	Q _{gd}			2.0		
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V f=1MHz		1450		pF
Output Capacitance	C _{oss}			285		
Reverse Transfer Capacitance	C _{rss}			145		
Turn-On Time	t _{d(on)}	V _{DD} =10V, R _L =1.3Ω I _D ≧8.0A, V _{GEN} =10V R _G =1Ω		10	20	ns
	t _r			10	20	
Turn-Off Time	t _{d(off)}			25	40	
	t _f			10	20	



Absolute Maximum Ratings (P-Channel)

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-20	V
Gate –Source Voltage	V _{GSS}	±12	V
Continuous Drain Current(T _J =150°C)	I _D	T _A =25°C	-9.0
		T _A =70°C	-8.0
Pulsed Drain Current	I _{DM}	-20	A
Continuous Source Current(Diode Conduction)	I _S	-1.7	A
Power Dissipation	P _D	T _A =25°C	3.5
		T _A =70°C	2.2
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	62.5	°C/W

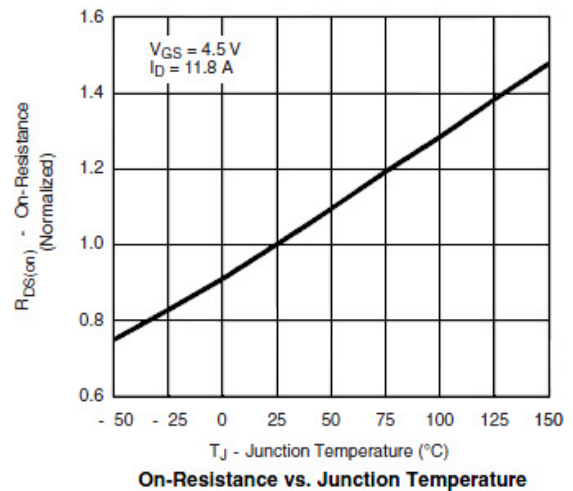
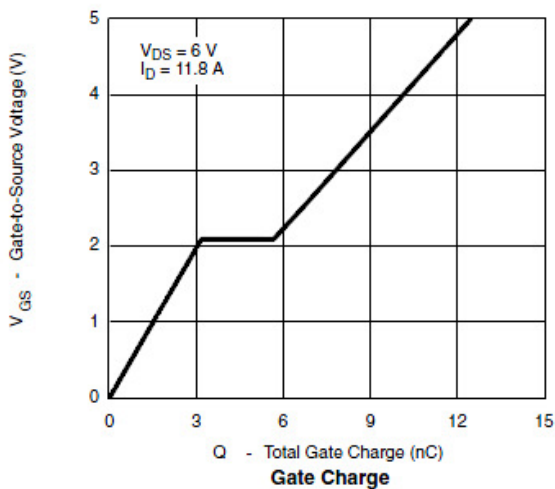
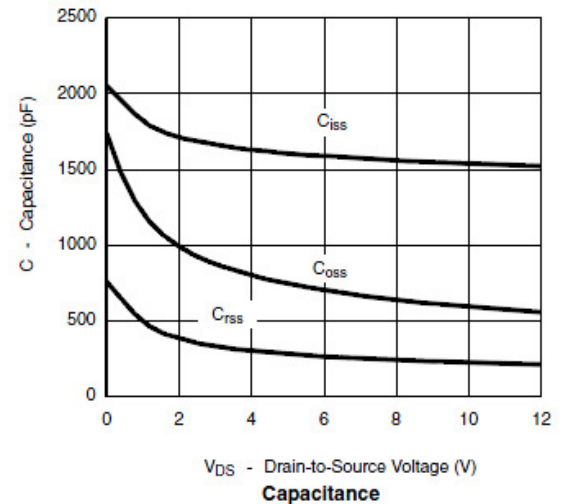
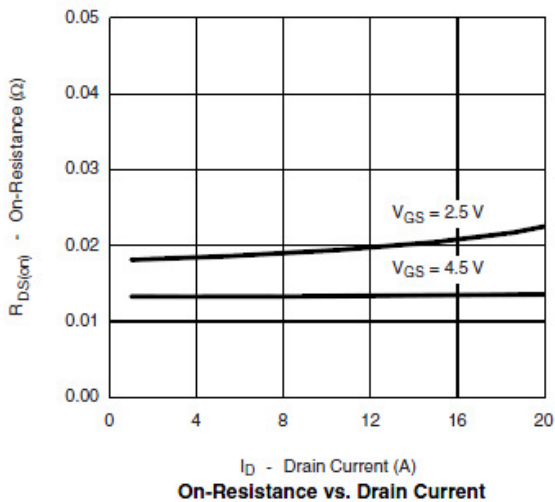
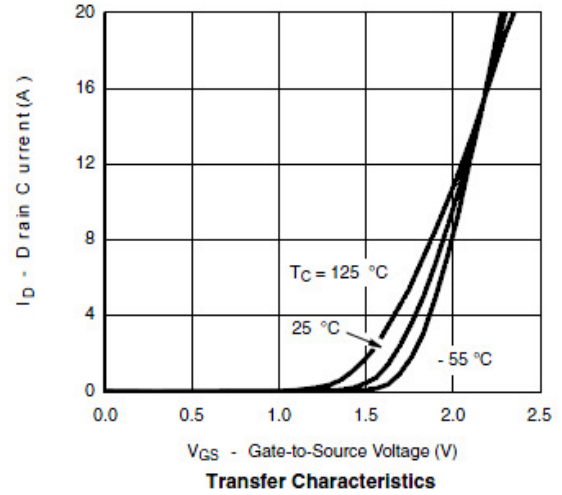
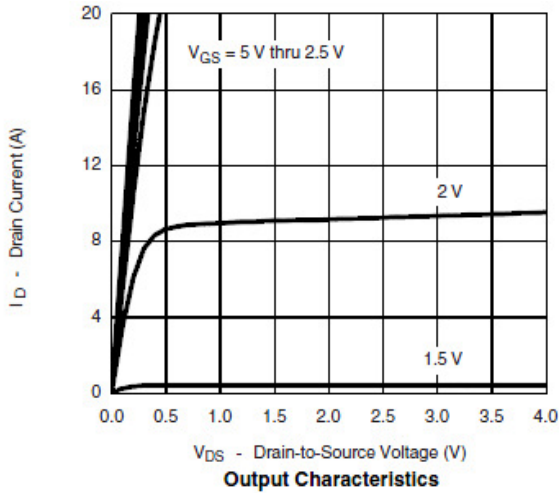
Electrical Characteristics (P-Channel)

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250uA	-20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-0.4		-1.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-16V, V _{GS} =0V			-1	uA
		V _{DS} =-16V, V _{GS} =0V T _J =85°C			-10	
On-State Drain Current	I _{D(on)}	V _{DS} ≤ -5V, V _{GS} =-4.5V	-10			A
		V _{DS} ≤ -5V, V _{GS} =-2.5V	-5			
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-9A		21	33	mΩ
		V _{GS} =-2.5V, I _D =-8A		32	42	
		V _{GS} =-1.8V, I _D =-6A		54	68	
Forward Transconductance	g _{FS}	V _{DS} =-9V, I _D =-6A		14		S
Diode Forward Voltage	V _{SD}	I _S =-2.5A, V _{GS} =0V		-0.85	-1.2	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =-15V, V _{GS} =-4.5V I _D ≡-6.0A		10	18	nC
Gate-Source Charge	Q _{gs}			1.6		
Gate-Drain Charge	Q _{gd}			3.0		
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V f=1MHz		950		pF
Output Capacitance	C _{oss}			200		
Reverse Transfer Capacitance	C _{rss}			175		
Turn-On Time	t _{d(on)}	V _{DD} =-15V, R _L =15Ω I _D ≡-5.0A, V _{GEN} =-10V R _G =6Ω		8	18	ns
	t _r			8	18	
Turn-Off Time	t _{d(off)}			25	50	
	t _f			25	35	

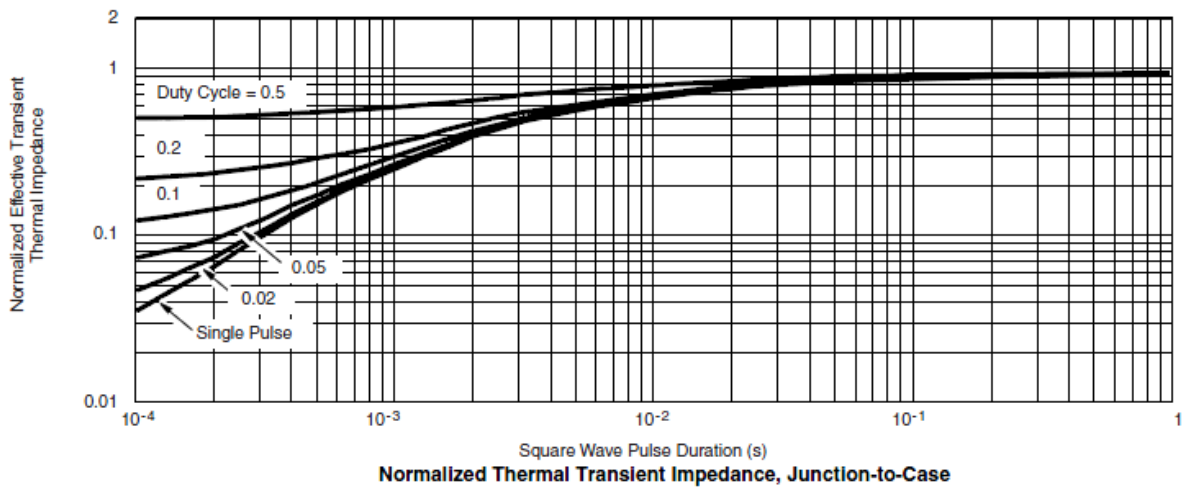
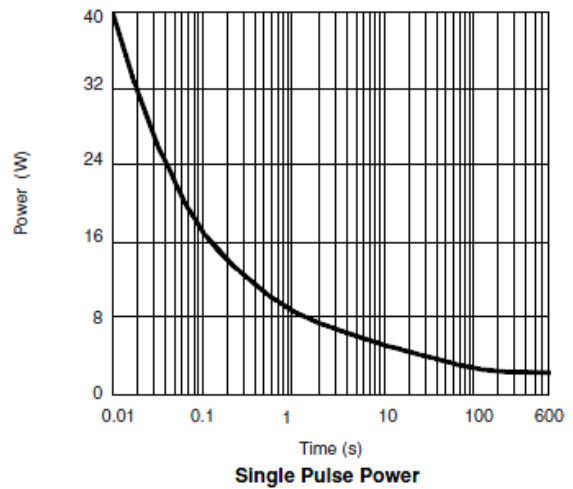
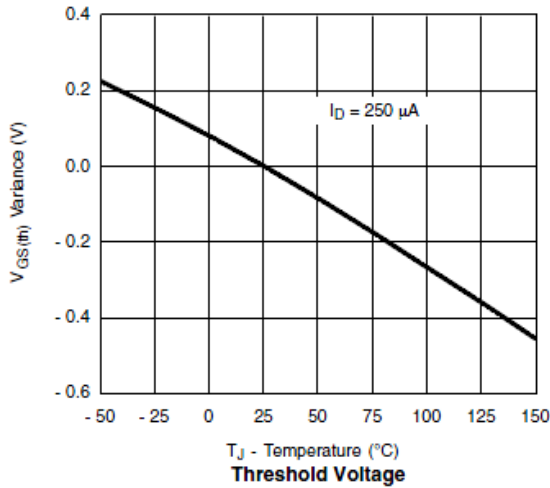
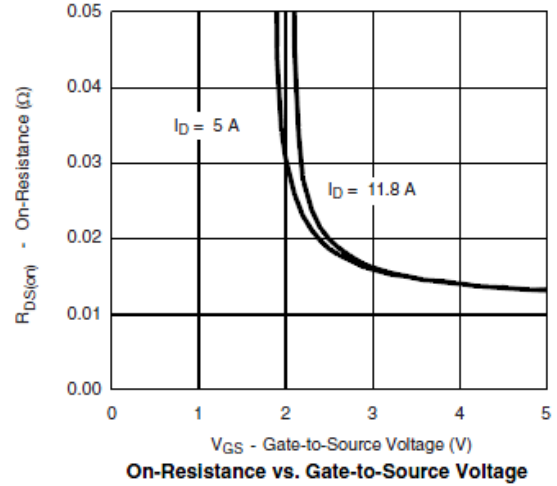
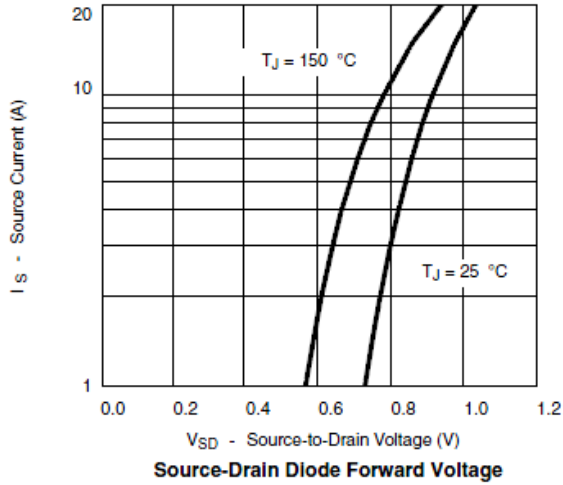


Typical Characteristics (N-Channel)



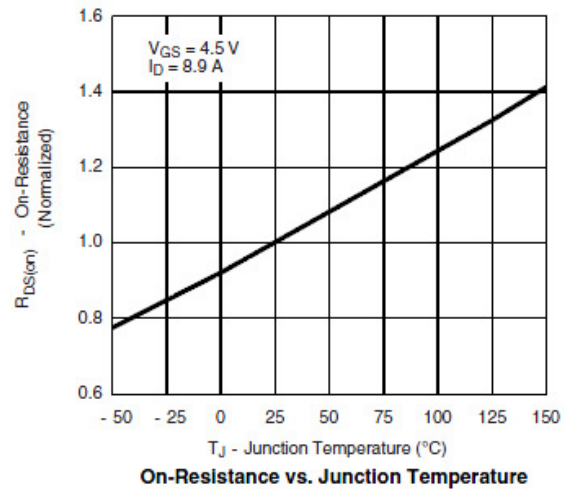
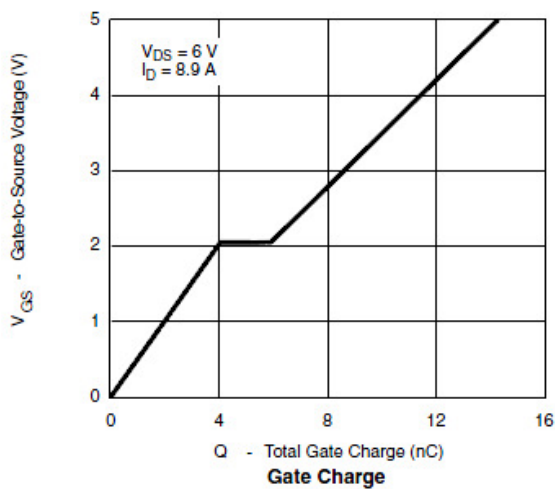
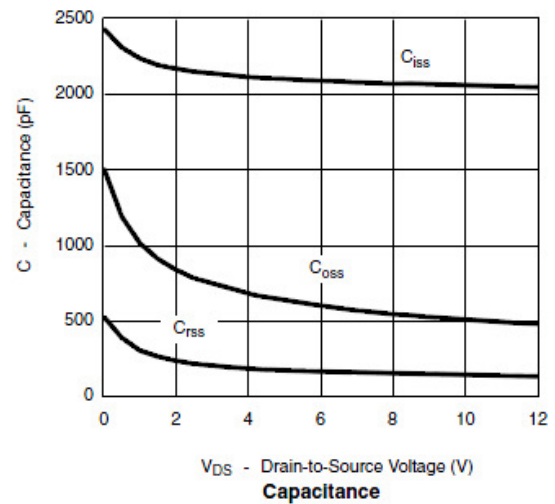
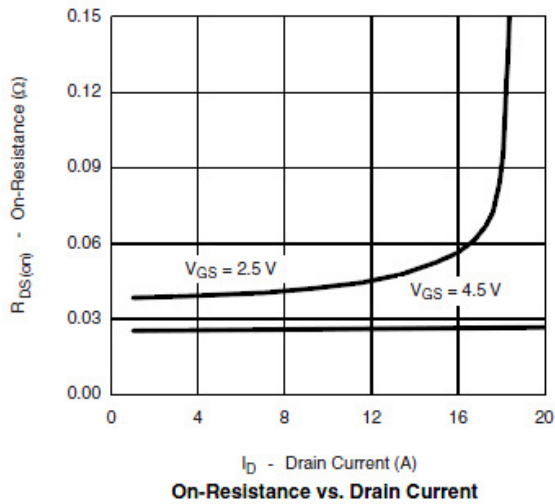
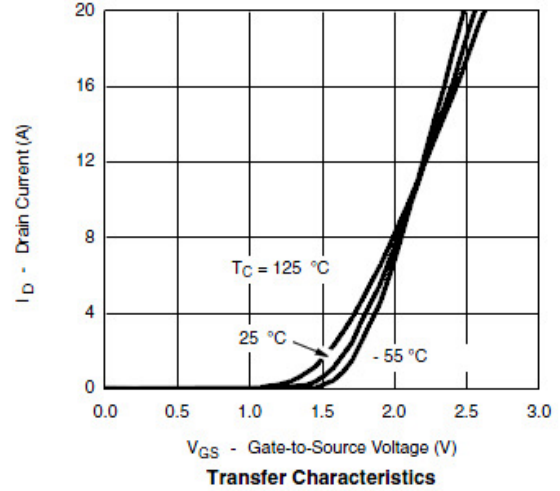
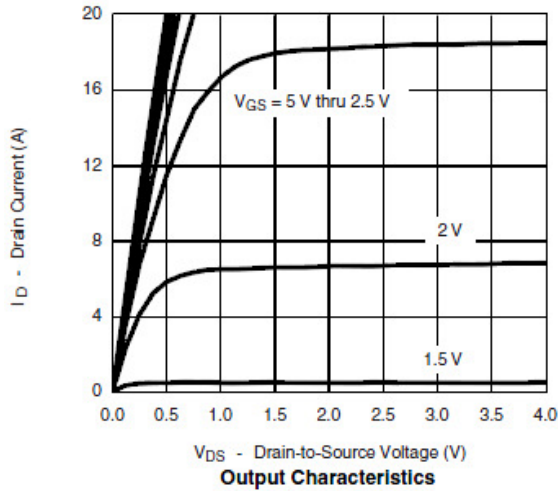


Typical Characteristics (N-Channel)



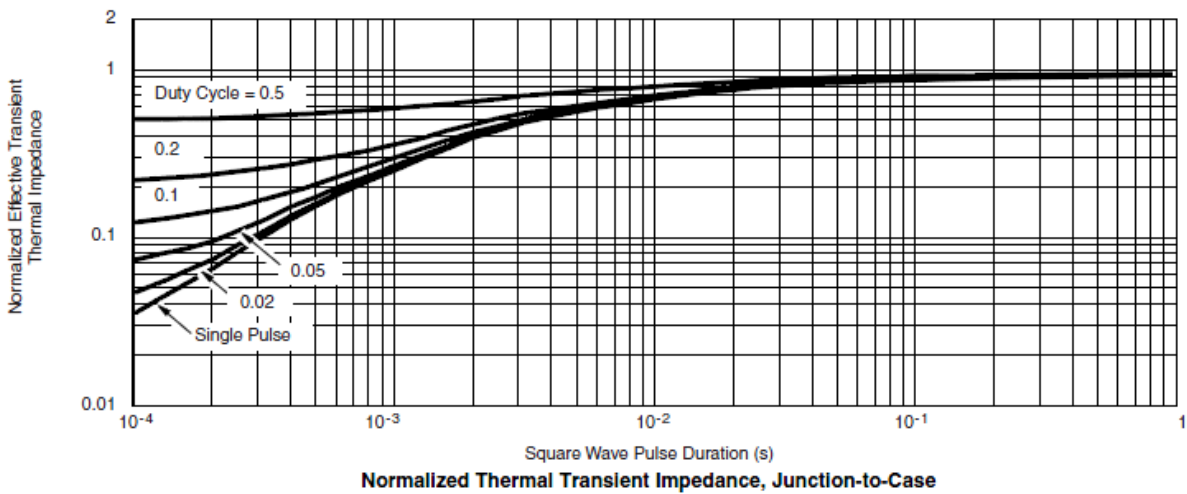
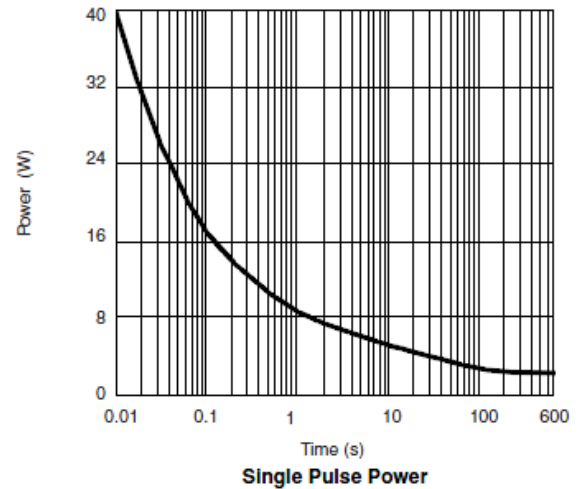
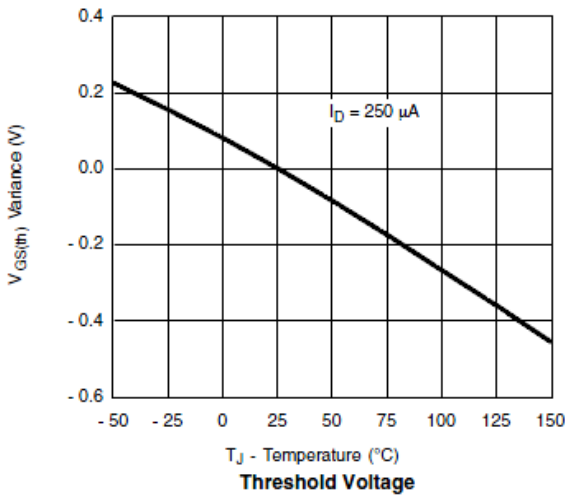
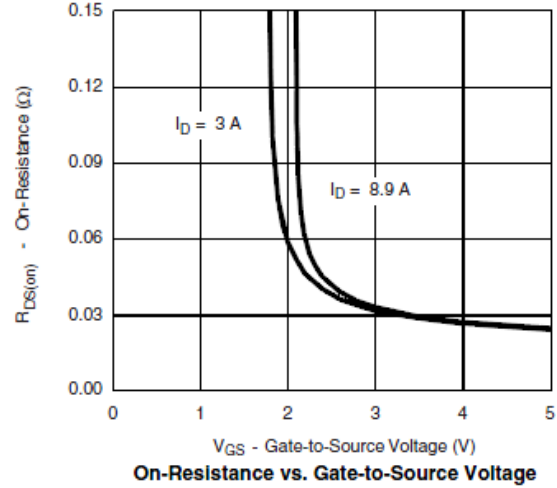
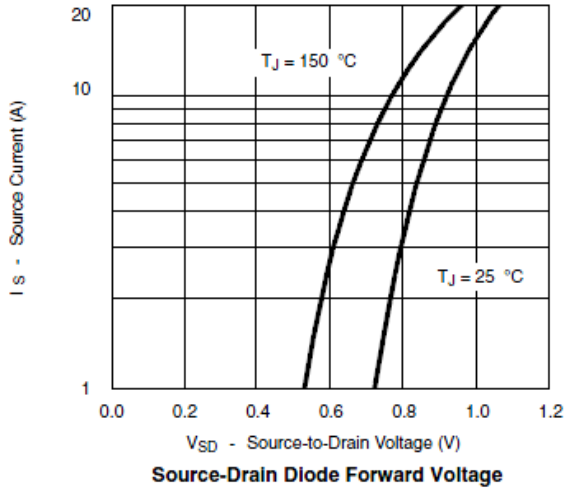


Typical Characteristics (P-Channel)





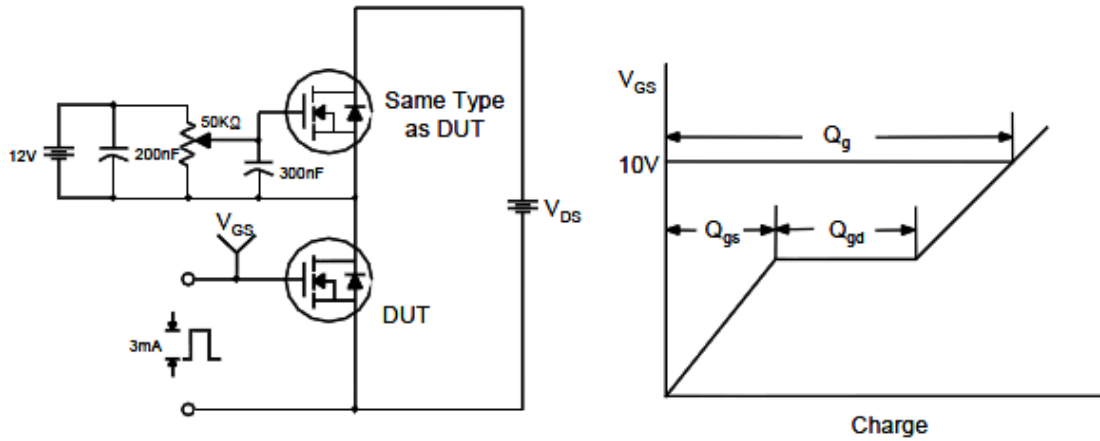
Typical Characteristics (P-Channel)



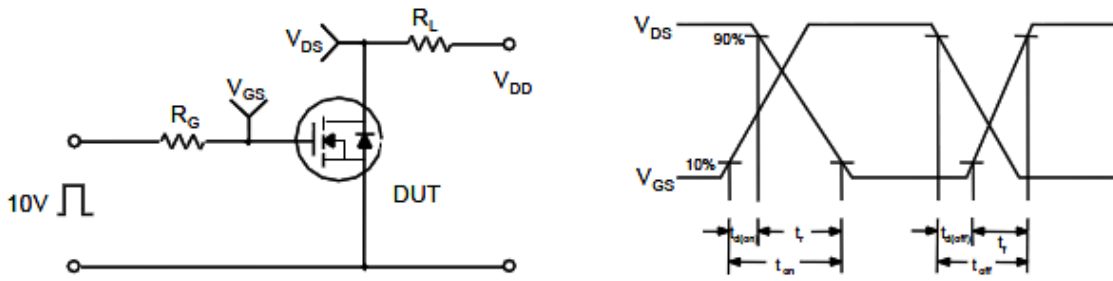


Typical Characteristics

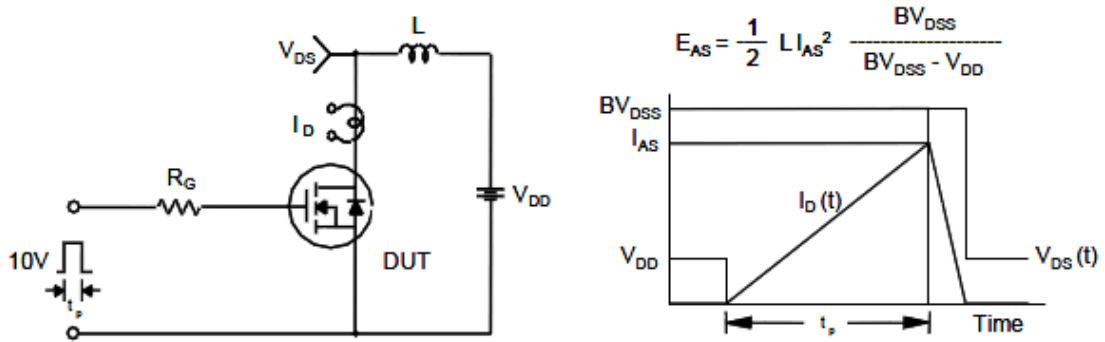
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

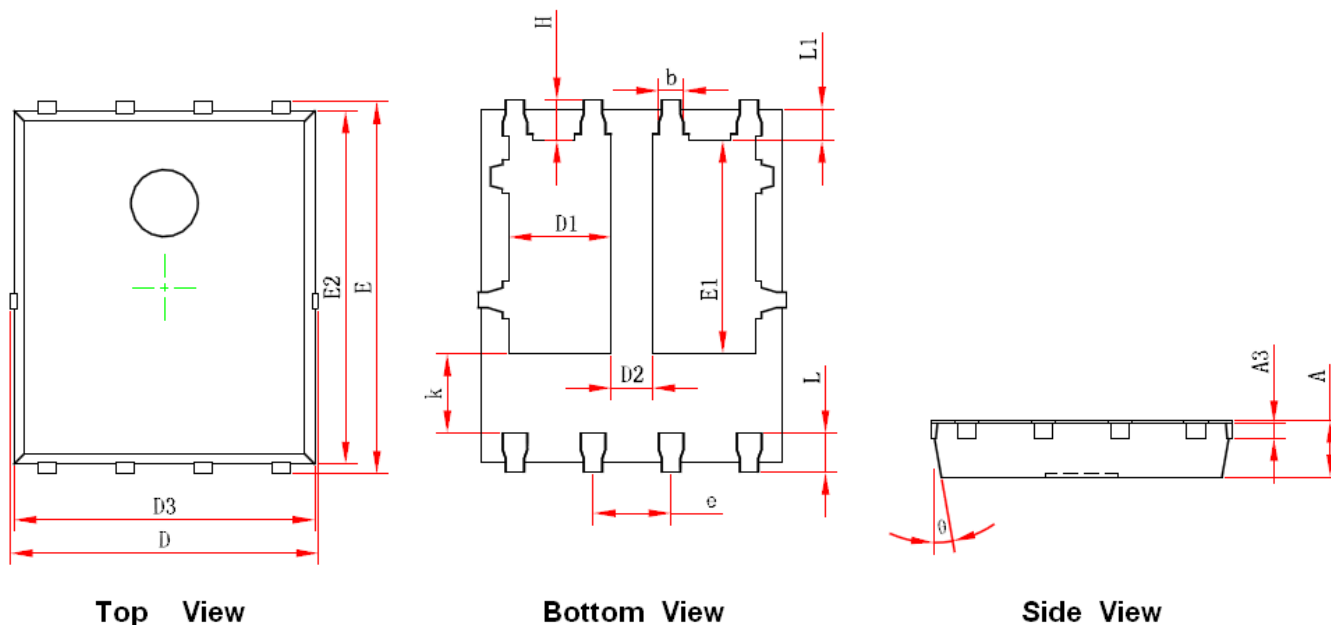


Unclamped Inductive Switching Test Circuit & Waveforms





Package Information (DFN 5X6-8L)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254 REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	1.470	1.870	0.058	0.074
D2	0.470	0.870	0.019	0.034
E1	3.375	3.575	0.133	0.141
D3	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

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2F, No.80, Sec.1, Cheng Kung Rd., Nan Kang Dist., Taipei City 115, Taiwan (R.O.C.)
Tel : 886 2) 2651 3928
Fax : 886 2) 2786 8483
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